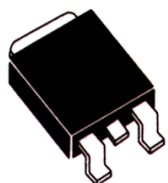




CJD200 NPN
CJD210 PNP

COMPLEMENTARY SILICON
POWER TRANSISTOR

DPAK **POWER!**™



DPAK CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CJD200, CJD210 types are Complementary Silicon Power Transistors manufactured in a surface mount package designed for high current amplifier applications.

MAXIMUM RATINGS (T_C=25°C)

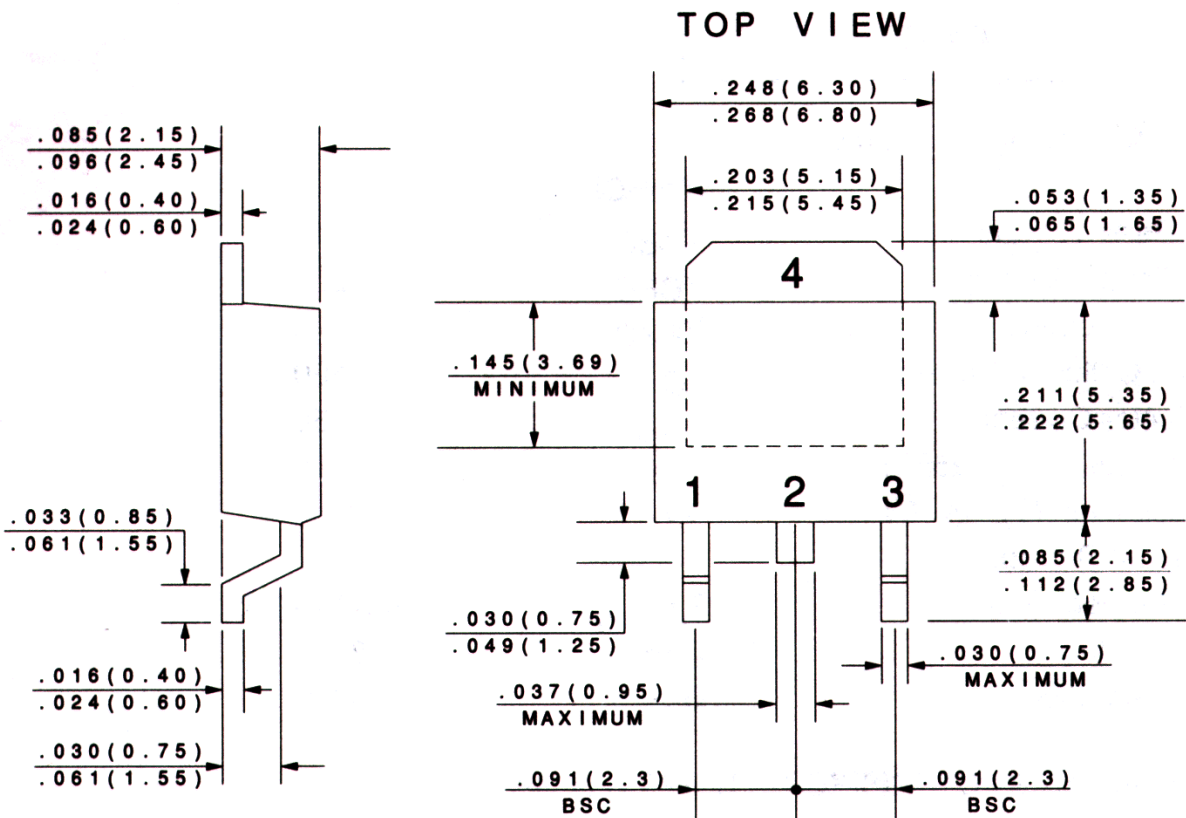
	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	25	V
Emitter-Base Voltage	V _{EBO}	8.0	V
Continuous Collector Current	I _C	5.0	A
Peak Collector Current	I _{CM}	10	A
Base Current	I _B	1.0	A
Power Dissipation (T _C =25°C)	P _D	12.5	W
Power Dissipation (T _A =25°C)	P _D	1.4	W
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JC}	10	°C/W
Thermal Resistance	θ _{JA}	89.3	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =40V		100	nA
I _{CBO}	V _{CB} =40V, T _C =125°C		100	μA
I _{EBO}	V _{EB} =8.0V		100	nA
BV _{CEO}	I _C =10mA	25		V
V _{CE} (SAT)	I _C =500mA, I _B =50mA		0.3	V
V _{CE} (SAT)	I _C =2.0A, I _B =200mA		0.75	V
V _{CE} (SAT)	I _C =5.0A, I _B =1.0A		1.8	V
V _{BE} (SAT)	I _C =5.0A, I _B =1.0A		2.5	V
V _{BE} (ON)	V _{CE} =1.0V, I _C =2.0A		1.6	V
h _{FE}	V _{CE} =1.0V, I _C =500mA	70		

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
h_{FE}	$V_{CE}=1.0V, I_C=2.0A$	45	180	
h_{FE}	$V_{CE}=2.0V, I_C=5.0A$	10		
f_T	$V_{CE}=10V, I_C=100mA, f=10MHz$	65		MHz
C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz$ (CJD200)		80	pF
C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz$ (CJD210)		120	pF

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR